2SC536N TRANSISTOR (NPN)

TO-92

1.EMITTER
2.COLLECTOR
3.BASE

FEATURES

- Large Current Capacity and Wide ASO.

APPLICATIONS

- Capable of Being Used in The Low Frequency to High Frequency Range.

ORDERING INFORMATION

Part Number	Package	Packing Method	Pack Quantity
2SC536N	TO-92	Bulk	1000pcs/Bag
2SC536N-TA	TO-92	Tape	2000pcs/Box

MAXIMUM RATINGS (T_a=25℃ unless otherwise noted)

Symbol	Parameter	Value	Unit
V_{CBO}	Collector-Base Voltage	60	V
V_{CEO}	Collector-Emitter Voltage	50	V
V_{EBO}	Emitter-Base Voltage	6	V
I_C	Collector Current	150	mA
P_C	Collector Power Dissipation	625	mW
$R_{\theta JA}$	Thermal Resistance From Junction To Ambient	200	℃ /W
T_J,T_{stg}	Operation Junction and Storage Temperature Range	-55~+150	℃

T_a=25℃ unless otherwise specified

Parameter	Symbol	Test conditions	Min	Typ	Max	Unit
Collector-base breakdown voltage	$V_{(BR)CBO}$	I_C= 0.01mA,I_E=0	60			V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	I_C=1mA,I_B=0	50			V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	I_E=0.01mA,I_C=0	6			V
Collector cut-off current	I_{CBO}	V_{CB}=40V,I_E=0			0.1	μA
Emitter cut-off current	I_{EBO}	V_{EB}=5V,I_C=0			0.1	μA
DC current gain	$h_{FE(1)}$	V_{CE}=6V, I_C=1mA	160		560	
	$h_{FE(2)}$	V_{CE}=6V, I_C=0.1mA	70			
Collector-emitter saturation voltage	$V_{CE(sat)}$	I_C=100mA,I_B=10mA			0.3	V
Base-emitter saturation voltage	$V_{BE\ (sat)}$	I_C=100mA,I_B=10mA			1	V
Collector output capacitance	C_{ob}	V_{CE}=6V, f=1MHz		3		pF
Transition frequency	f_T	V_{CE}=6V,I_C= 10mA		200		MHz

CLASSIFICATION OF $h_{FE(1)}$

RANK	F	G
RANGE	160-320	280-560